

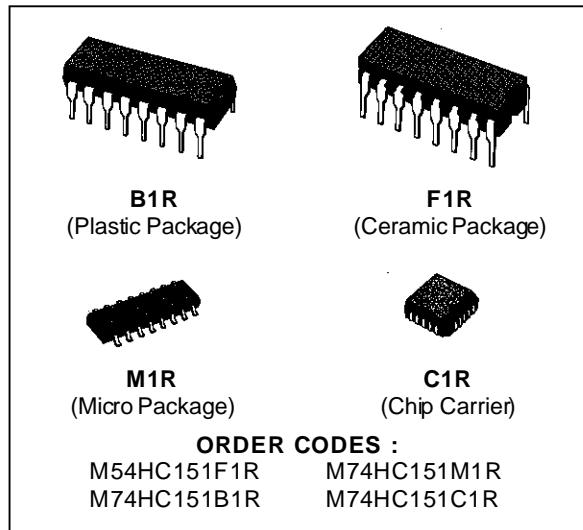
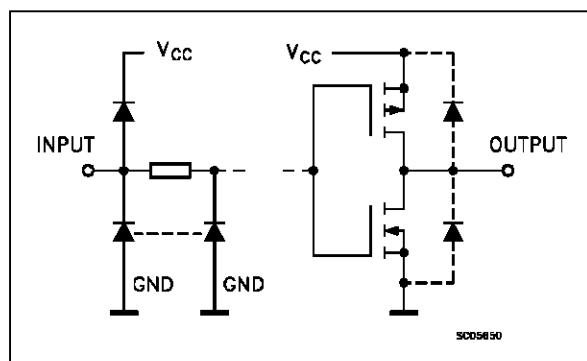
8 CHANNEL MULTIPLEXER

- HIGH SPEED
 $t_{PD} = 15 \text{ ns (TYP.)}$ AT $V_{CC} = 5 \text{ V}$
 - LOW POWER DISSIPATION
 $I_{CC} = 4 \mu\text{A (MAX.)}$ AT $T_A = 25^\circ\text{C}$
 - HIGH NOISE IMMUNITY
 $V_{NIH} = V_{NIL} = 28 \% V_{CC}$ (MIN.)
 - OUTPUT DRIVE CAPABILITY
10 LS-TTL LOADS
 - SYMMETRICAL OUTPUT IMPEDANCE
 $|I_{OH}| = I_{OL} = 4 \text{ mA (MIN.)}$
 - BALANCED PROPAGATION DELAYS
 $t_{PLH} = t_{PHL}$
 - WIDE OPERATING VOLTAGE RANGE
 V_{CC} (OPR) = 2 V TO 6 V
 - PIN AND FUNCTION COMPATIBLE
WITH 54/74LS151

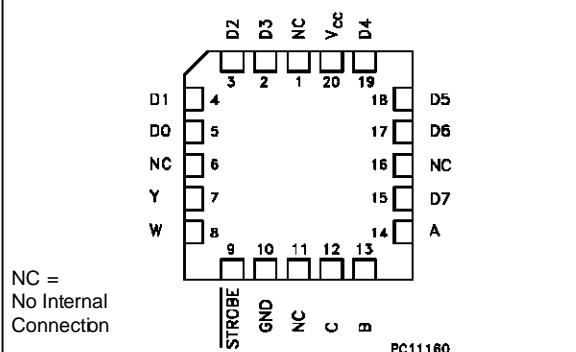
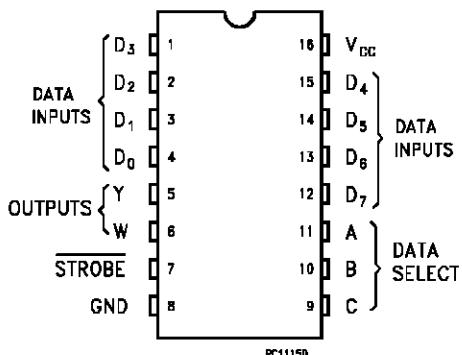
DESCRIPTION

The M54/74HC151 is a high speed CMOS 8 CHANNEL MULTIPLEXER fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption. It provides, in one package, the ability to select one bit of data from up to eight sources. The HC151 can be used as a universal function generator to generate any logic function of four variables. Outputs Y and W are complementary selection depends on the address inputs A, B and C. The strobe input must be taken low to enable this device, when the strobe is high W output is forced high and consequently Y output goes low. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN CONNECTIONS (top view)



M54/M74HC151

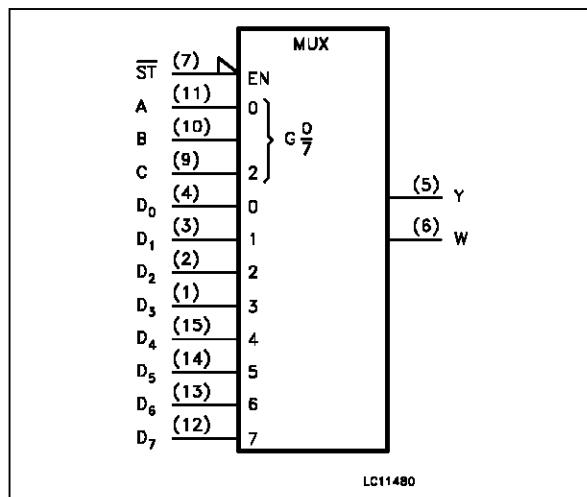
TRUTH TABLE

INPUTS			STROBE \bar{S}	OUTPUTS	
C	B	A		Y	W
X	X	X	H	L	H
L	L	L	L	D0	$\overline{D0}$
L	L	H	L	D1	$\overline{D1}$
L	H	L	L	D2	$\overline{D2}$
L	H	H	L	D3	$\overline{D3}$
H	L	L	L	D4	$\overline{D4}$
H	L	H	L	D5	$\overline{D5}$
H	H	L	L	D6	$\overline{D6}$
H	H	H	L	D7	$\overline{D7}$

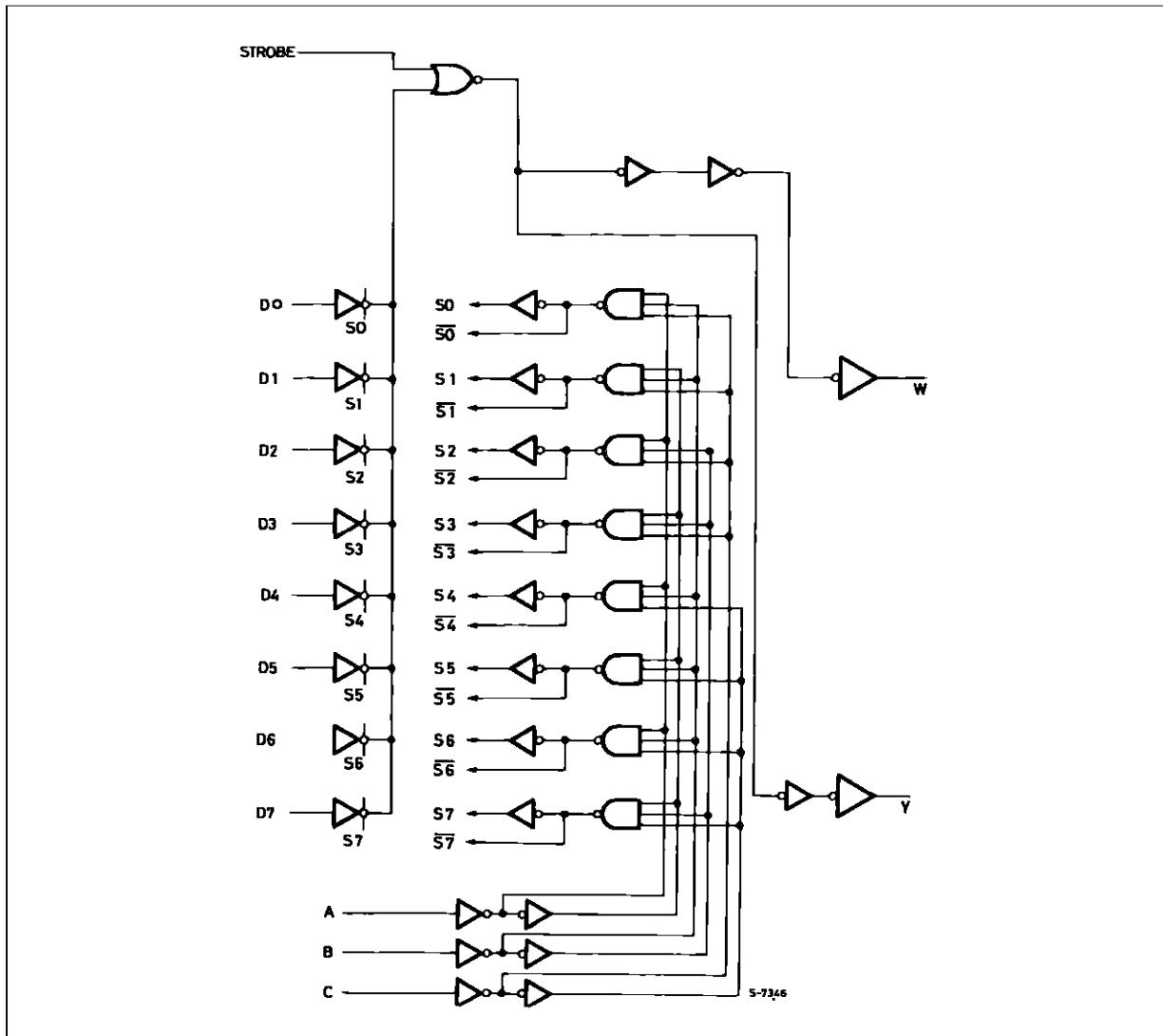
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
4, 3, 2, 1, 15, 14, 13, 12	D0 to D7	Multiplexer Inputs
5	y	Multiplexer Output
6	w	Complementary Multiplexer Output
7	STROBE	Strobe Input
11, 10, 9	A, B, C	Select Inputs
8	GND	Ground (0V)
16	Vcc	Positive Supply Voltage

IEC LOGIC SYMBOL



LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Source Sink Current Per Output Pin	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P _D	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

(*) 500 mW: $\leq 65^{\circ}\text{C}$ derate to 300 mW by $10\text{mW}/^{\circ}\text{C}$: 65°C to 85°C

M54/M74HC151

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value			Unit	
V _{CC}	Supply Voltage	2 to 6			V	
V _I	Input Voltage	0 to V _{CC}			V	
V _O	Output Voltage	0 to V _{CC}			V	
T _{OP}	Operating Temperature: M54HC Series M74HC Series	-55 to +125 -40 to +85			°C °C	
t _r , t _f	Input Rise and Fall Time	V _{CC} = 2 V	0 to 1000		ns	
		V _{CC} = 4.5 V	0 to 500			
		V _{CC} = 6 V	0 to 400			

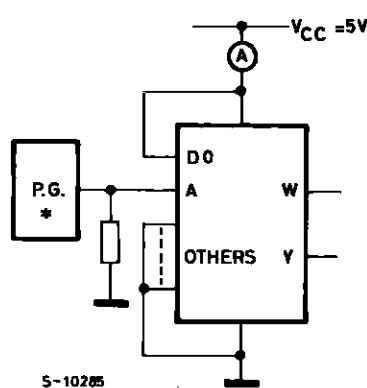
DC SPECIFICATIONS

Symbol	Parameter	Test Conditions		Value						Unit	
		V _{CC} (V)		T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input Voltage	2.0		1.5			1.5		1.5		V
		4.5		3.15			3.15		3.15		
		6.0		4.2			4.2		4.2		
V _{IL}	Low Level Input Voltage	2.0			0.5		0.5		0.5		V
		4.5			1.35		1.35		1.35		
		6.0			1.8		1.8		1.8		
V _{OH}	High Level Output Voltage	2.0	V _I = V _{IH} or V _{IL}	1.9	2.0		1.9		1.9		V
		4.5		4.4	4.5		4.4		4.4		
		6.0		5.9	6.0		5.9		5.9		
		4.5		I _O =-4.0 mA	4.18	4.31	4.13		4.10		
		6.0		I _O =-5.2 mA	5.68	5.8	5.63		5.60		
V _{OL}	Low Level Output Voltage	2.0	V _I = V _{IH} or V _{IL}		0.0	0.1		0.1		0.1	V
		4.5			0.0	0.1		0.1		0.1	
		6.0			0.0	0.1		0.1		0.1	
		4.5		I _O = 4.0 mA		0.17	0.26		0.33	0.40	
		6.0		I _O = 5.2 mA		0.18	0.26		0.33	0.40	
I _I	Input Leakage Current	6.0	V _I = V _{CC} or GND			±0.1		±1		±1	µA
I _{CC}	Quiescent Supply Current	6.0	V _I = V _{CC} or GND			4		40		80	µA

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

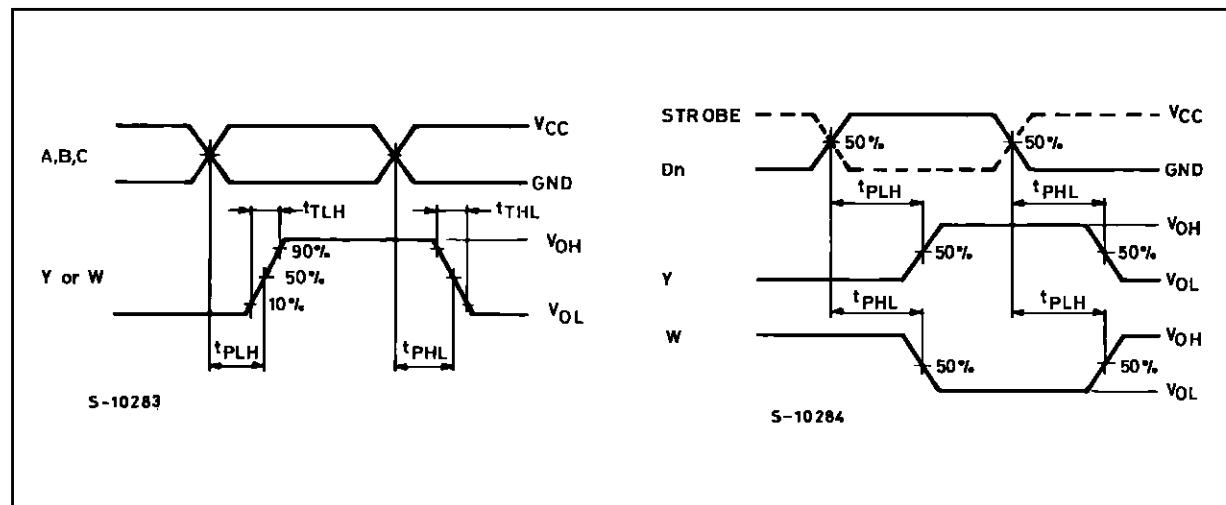
Symbol	Parameter	Test Conditions		Value						Unit	
		V _{CC} (V)		T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t _{TLH} t _{THL}	Output Transition Time	2.0 4.5 6.0			30	75		95		110	ns
					8	15		19		22	
					7	13		16		19	
t _{P LH} t _{PHL}	Propagation Delay Time (D - W)	2.0 4.5 6.0			56	130		165		190	ns
					16	26		33		38	
					14	22		28		32	
t _{P LH} t _{PHL}	Propagation Delay Time (D - Y)	2.0 4.5 6.0			56	130		165		190	ns
					16	26		33		38	
					14	22		28		32	
t _{P LH} t _{PHL}	Propagation Delay Time (STROBE - W)	2.0 4.5 6.0			30	85		105		125	ns
					10	17		21		25	
					9	14		18		21	
t _{P LH} t _{PHL}	Propagation Delay Time (STROBE - Y)	2.0 4.5 6.0			30	85		105		125	ns
					10	17		21		25	
					9	14		18		21	
t _{P LH} t _{PHL}	Propagation Delay Time (A, B, C - W)	2.0 4.5 6.0			72	160		200		235	ns
					20	32		40		47	
					17	27		34		40	
t _{P LH} t _{PHL}	Propagation Delay Time (A, B, C - Y)	2.0 4.5 6.0			72	160		200		235	ns
					20	32		40		47	
					17	27		34		40	
C _{IN}	Input Capacitance				5	10		10		10	pF
C _{PD} (*)	Power Dissipation Capacitance				63						pF

(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I_{cc}(opr) = C_{PD} • V_{CC} • f_{IN} + I_{cc}

TEST CIRCUIT I_{cc} (Opr.)

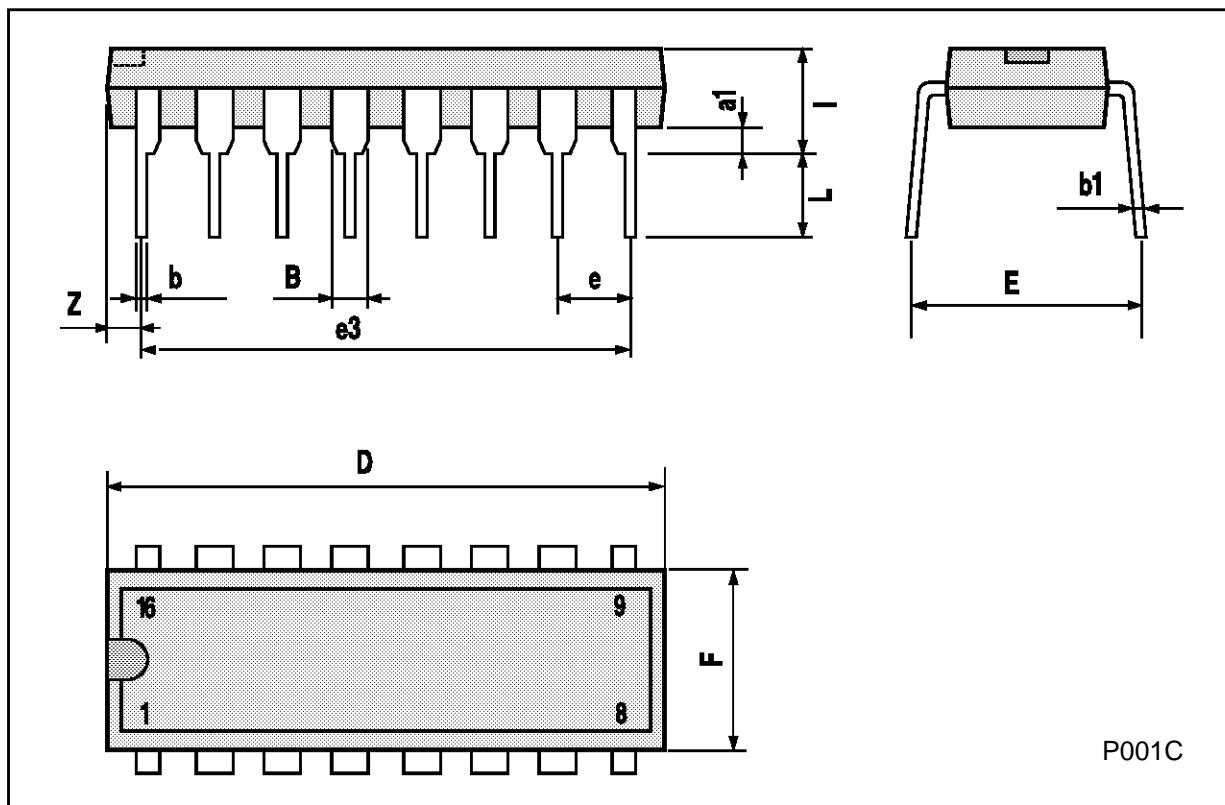
* INPUT WAVEFORM IS THE SAME AS THAT IN CASE OF SWITCHING CHARACTERISTICS TEST.

SWITCHING CHARACTERISTICS TEST WAVEFORM



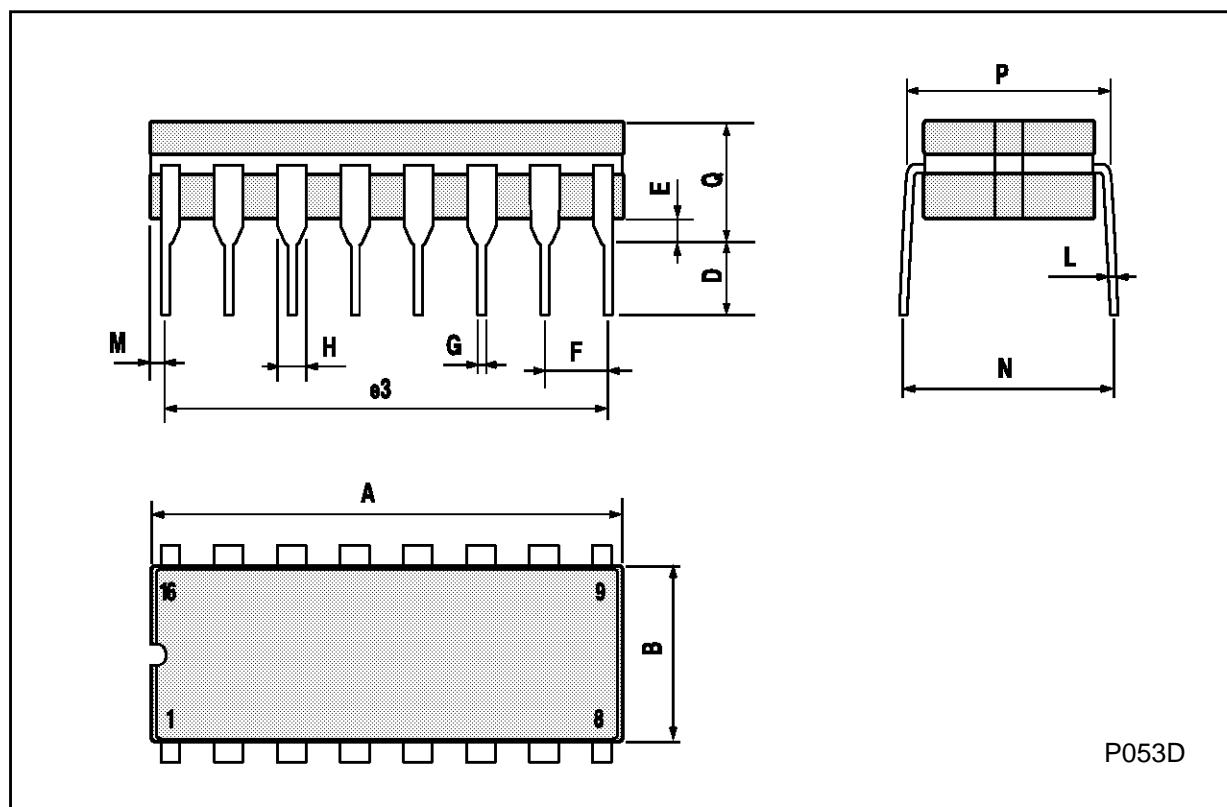
Plastic DIP16 (0.25) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



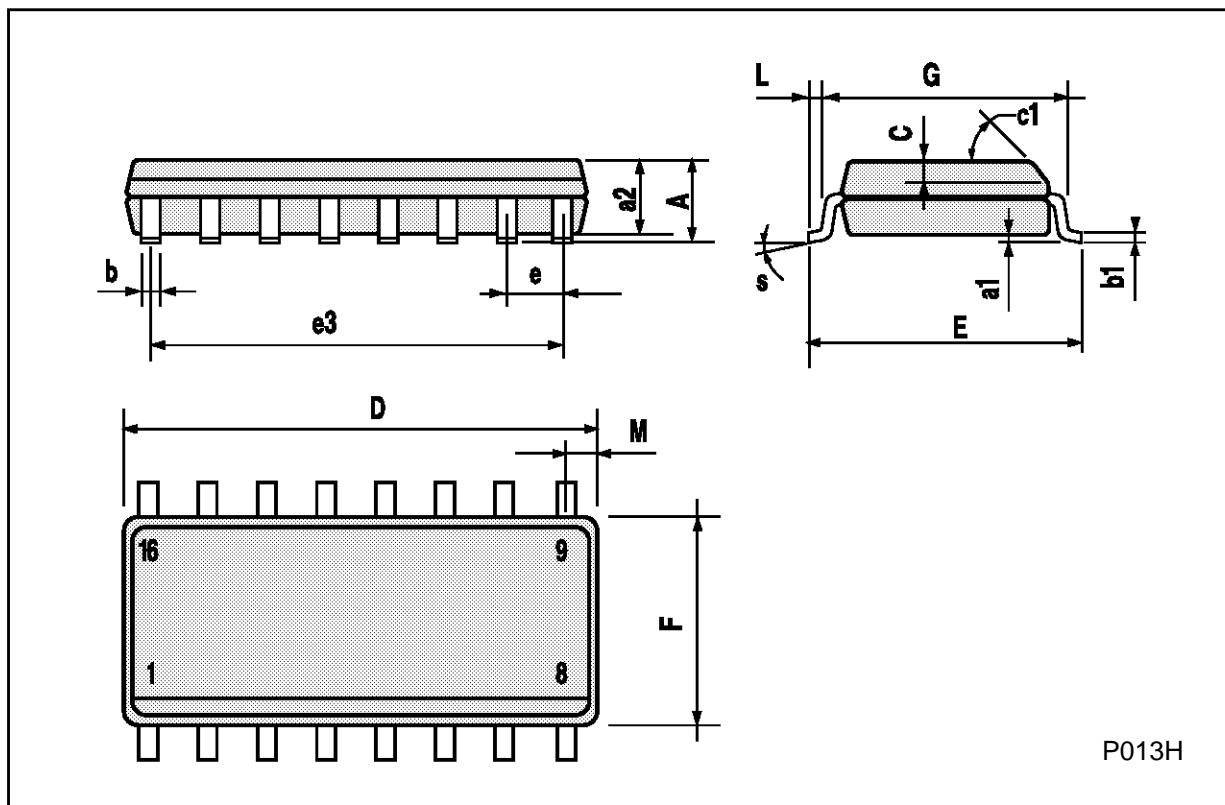
Ceramic DIP16/1 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



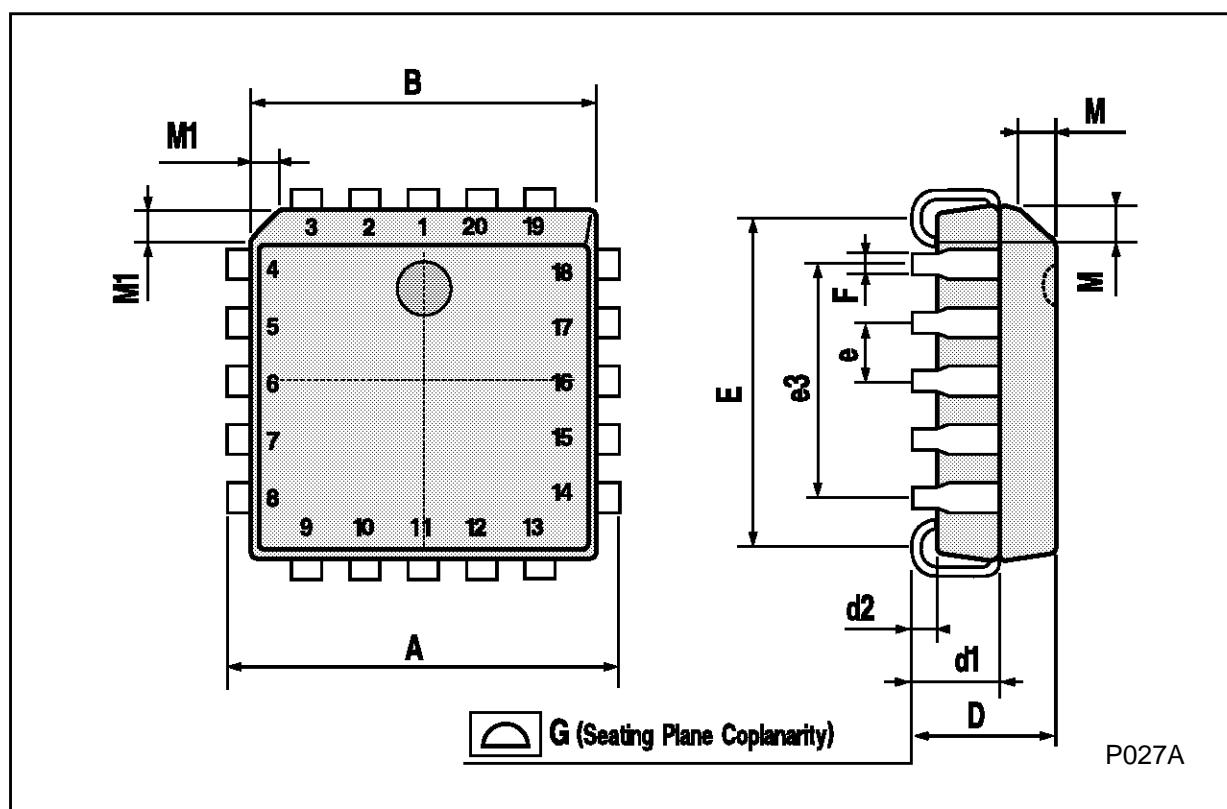
SO16 (Narrow) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.004		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1			45° (typ.)			
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S			8° (max.)			



PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



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